

# JS210N18

High Efficiency HJT Cell

## Advantages



### Efficiency

Average efficiency over 25%



### Power Generation

Power generation gain up to 5%+



### Bifacial Coefficient

High bifacial coefficient of > 95%



### Technique

4-6 step technique



### Wastewater

Zero NH<sub>3</sub>-N Wastewater



### Mass Production

Mass production capability of 120um-thick silicon



### Temperature

Production temperature less than 250°C



### Yield

Average yield up to 98%



### No Attenuation

No PID.LID effect



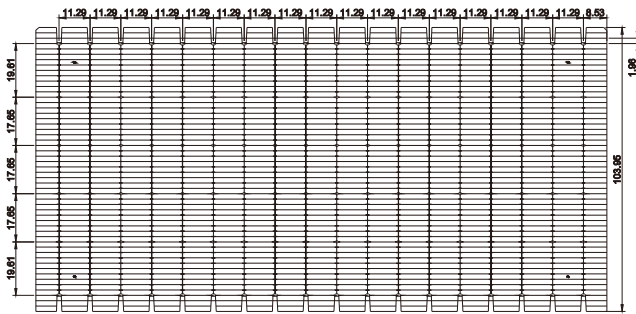
### Temperature Coefficient

Lower temperature coefficient

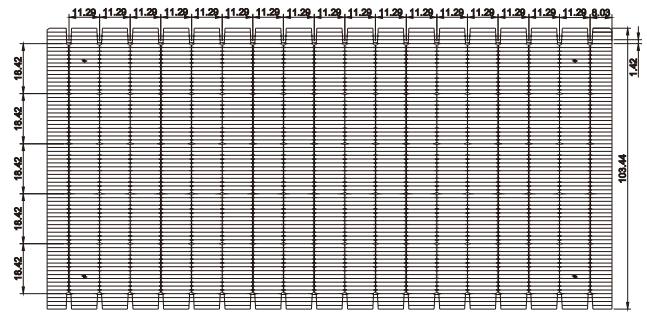
## Product Specification

Size	210 mm*105 mm ±0.25 mm
Material	N-type mono crystalline silicon
Thickness	120 ± 20 μm

## Solar Cell Structure



Front Side



Back Side

## Electrical performance

Eff(%)	Pmpp(W)	Uoc(V)	Isc(A)	FF(%)	Umpp(V)	Impp(A)
26.0	5.73	0.752	8.806	86.61	0.682	8.410
25.9	5.71	0.751	8.797	86.42	0.681	8.382
25.8	5.69	0.751	8.772	86.38	0.680	8.368
25.7	5.67	0.750	8.748	86.36	0.679	8.340
25.6	5.64	0.750	8.730	86.30	0.679	8.327
25.5	5.62	0.749	8.719	86.21	0.678	8.315
25.4	5.60	0.749	8.687	86.19	0.678	8.276
25.3	5.58	0.748	8.672	86.10	0.677	8.261
25.2	5.56	0.748	8.658	85.91	0.676	8.238
25.1	5.53	0.748	8.631	85.88	0.675	8.218
25.0	5.51	0.747	8.623	85.52	0.674	8.186
24.9	5.49	0.747	8.604	85.48	0.673	8.172
24.8	5.47	0.747	8.592	85.30	0.672	8.149
24.7	5.45	0.746	8.586	85.11	0.671	8.135
24.6	5.42	0.746	8.577	84.87	0.670	8.115

Standard test conditions: AM 1.5, 1000W/m<sup>2</sup>, 25°C